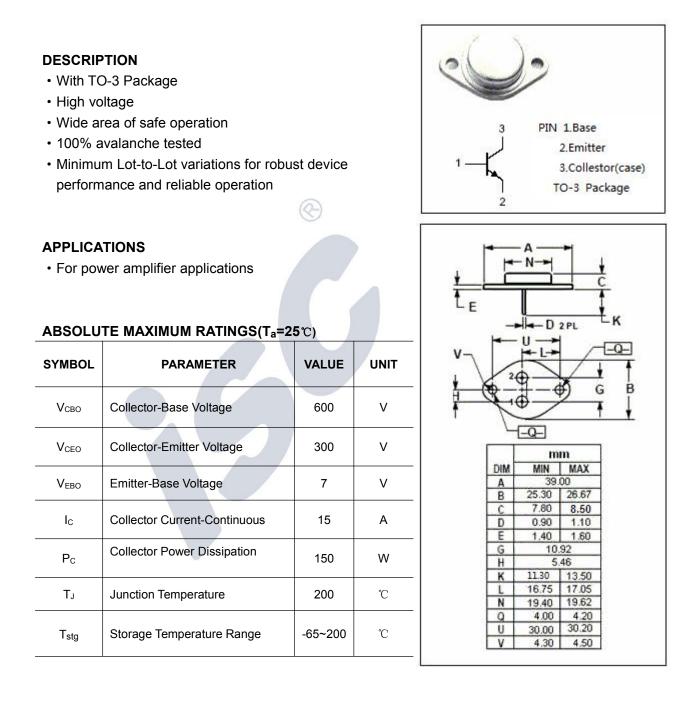


isc Silicon NPN Power Transistor

2SC1141





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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	мах	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.6	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	300			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7			V
h _{FE-1}	DC Current Gain	I _C =1.0A; V _{CE} = 5V	15		50	
hfe-2	DC Current Gain	I _C =7.5A; V _{CE} = 5V	10		25	
fT	Current-Gain—Bandwidth Product	Ic= 1.0A; V _{CE} = 12V; f _{test} = 1MHz	10			MHz

NOTICE:

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